

SSC2500GN1

N-Channel Enhancement Mode MOSFET with ESD protection

Features

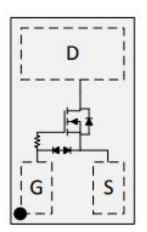
VDS	VGS	RDSON Typ.	ID	ESD
		195mR@4V5		
20V	±8V	240mR@2V5	1.1A	2K
		305mR@1V8		

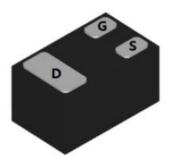
> Description

This device is a N-Channel enhancement mode MOSFET which is produced with high cell density and DMOS trench technology. This device particularly suits low voltage applications, especially for battery powered circuits, the tiny and thin outline saves PCB consumption.

> Pin configuration

Top view





Bottom View

> Applications

- Load Switch
- Portable Devices
- DCDC conversion

> Ordering Information

Device	Package	Shipping
SSC2500GN1	DFN1006	10K/Reel



Marking



> **Absolute Maximum Ratings**(T_A=25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain-to-Source Voltage	20	V
V _{GSS}	Gate-to-Source Voltage	±8	V
ID	Continuous Drain Current ^a	1.1	А
I _{DM}	Pulsed Drain Current ^b	3.1	А
PD	Power Dissipation ^c	0.32	W
P _{DSM}	Power Dissipation ^a	0.18	W
TJ	Operation junction temperature	-55 to 150	°C
T _{STG}	Storage temperature range	-55 to 150	°C

> Thermal Resistance Ratings($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
R _{0JA}	Junction-to-Ambient Thermal Resistance		690	
	а			°C/W
R _{θJC}	Junction-to-Case Thermal Resistance		379	

Note:

- a. The value of RθJA is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with TA=25°C. The value in any given application depends on the user is specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation PD is based on TJ(MAX)=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

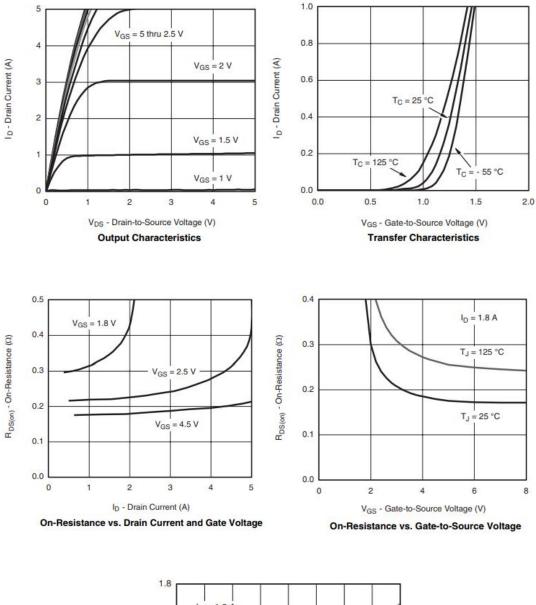


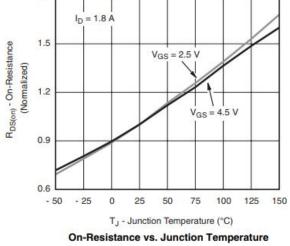
Electronics Characteristics(T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Мах	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	20			V
V _{GS (th)}	Gate Threshold Voltage	VDS=VGS,ID=250uA	0.5	0.68	1	V
		VGS=4.5V,ID=0.5A		195	310	
R _{DS(on)}	Drain-Source	VGS=2.5V,ID=0.5A		240	380	mR
	On-Resistance	VGS=1.8V,ID=0.35A		305	800	
I _{DSS}	Zero Gate Voltage Drain Current	VDS=20V,VGS=0V			1	uA
I _{GSS}	Gate-Source leak current	VGS=±8V,VDS=0V			±10	uA
G _{FS}	Forward Transconductance	VDS=5V,ID=0.5A		2		S
V _{SD}	Forward Voltage	VGS=0V,IS=0.5A		0.7	1.3	V
Ciss	Input Capacitance			66		
Coss	Output Capacitance	VDS=10V, VGS=0V, F=1MHZ		18		pF
Crss	Reverse Transfer Capacitance			9		
T _{D(ON)}	Turn-on delay time	VGS=4.5V,		20		
T _{D(OFF)}	Turn-off delay time	VDS=10V, RG=6R,ID=0.6A		40		ns



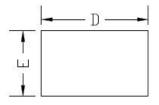
> Typical Characteristics(T_A=25°C unless otherwise noted)



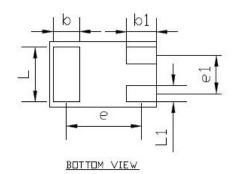


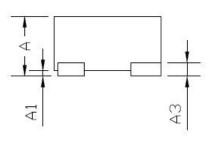


Package Information



A ATTAL A
VIEW





SIDE VIEW

PKG	DFN1006			
REF.	MIN.	NDM.	MAX	
Α	>0.4	-	0,50	
A1	0,00	(1 14)	0.05	
A3	0.125REF			
D	0,95	1.00	1.05	
E	0.55	0.60	0.65	
ø	0,20	0.25	0.30	
b1	0,20	0,30	0,40	
L	0.45	0.50	0.55	
L1	0,10	0.15	0,20	
е	0,675			
e1		0,35		

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